

**RADIATION HARDENED  
 LOGIC LEVEL POWER MOSFET  
 THRU-HOLE (TO-39)**

**2N7610T2  
 IRHLF77214  
 250V, N-CHANNEL  
 R7™ TECHNOLOGY**

**Product Summary**

Part Number	Radiation Level	RDS(on)	ID
IRHLF77214	100K Rads (Si)	1.0Ω	3.3A
IRHLF73214	300K Rads (Si)	1.0Ω	3.3A



International Rectifier's R7™ Logic Level Power MOSFETs provide simple solution to interfacing CMOS and TTL control circuits to power devices in space and other radiation environments. The threshold voltage remains within acceptable operating limits over the full operating temperature and post radiation. This is achieved while maintaining single event gate rupture and single event burnout immunity.

The device is ideal when used to interface directly with most logic gates, linear IC's, micro-controllers, and other device types that operate from a 3.3-5V source. It may also be used to increase the output current of a PWM, voltage comparator or an operational amplifier where the logic level drive signal is available.

**Features:**

- 5V CMOS and TTL Compatible
- Fast Switching
- Single Event Effect (SEE) Hardened
- Low Total Gate Charge
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Light Weight

**Absolute Maximum Ratings**

**Pre-Irradiation**

	Parameter		Units
ID @ VGS = 4.5V, TC=25°C	Continuous Drain Current	3.3	A
ID @ VGS = 4.5V, TC=100°C	Continuous Drain Current	2.1	
IDM	Pulsed Drain Current ①	13.2	
PD @ TC = 25°C	Max. Power Dissipation	22.7	W
	Linear Derating Factor	0.18	W/°C
VGS	Gate-to-Source Voltage	±10	V
EAS	Single Pulse Avalanche Energy ②	29	mJ
IAR	Avalanche Current ①	3.3	A
EAR	Repetitive Avalanche Energy ①	2.3	mJ
dv/dt	Peak Diode Recovery dv/dt ③	3.29	V/ns
TJ	Operating Junction	-55 to 150	°C
TSTG	Storage Temperature Range		
	Lead Temperature	300 (0.063in/1.6mm from case for 10s)	
	Weight	0.98 (Typical)	g

For footnotes refer to the last page

www.irf.com

Electrical Characteristics @ T<sub>j</sub> = 25°C (Unless Otherwise specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
B <sub>V</sub> DSS	Drain-to-Source Breakdown Voltage	250	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔB <sub>V</sub> DSS/ΔT <sub>J</sub>	Temperature Coefficient of Breakdown Voltage	—	0.22	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1.0mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-State Resistance	—	—	1.0	Ω	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 2.1A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	1.0	—	2.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
ΔV <sub>GS(th)</sub> /ΔT <sub>J</sub>	Gate Threshold Voltage Coefficient	—	-5.2	—	mV/°C	
g <sub>fs</sub>	Forward Transconductance	2.5	—	—	S	V <sub>DS</sub> = 15V, I <sub>DS</sub> = 2.1A ④
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	—	—	1.0	μA	V <sub>DS</sub> = 200V, V <sub>GS</sub> = 0V
		—	—	10		V <sub>DS</sub> = 200V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Leakage Forward	—	—	100	nA	V <sub>GS</sub> = 10V
I <sub>GSS</sub>	Gate-to-Source Leakage Reverse	—	—	-100		V <sub>GS</sub> = -10V
Q <sub>g</sub>	Total Gate Charge	—	—	18	nC	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 3.3A
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	5.0		V <sub>DS</sub> = 125V
Q <sub>gd</sub>	Gate-to-Drain ('Miller') Charge	—	—	12		
t <sub>d(on)</sub>	Turn-On Delay Time	—	—	27	ns	V <sub>DD</sub> = 125V, I <sub>D</sub> = 3.3A, V <sub>GS</sub> = 5.0V, R <sub>G</sub> = 7.5Ω
t <sub>r</sub>	Rise Time	—	—	57		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	—	45		
t <sub>f</sub>	Fall Time	—	—	55		
L <sub>S</sub> + L <sub>D</sub>	Total Inductance	—	7.0	—	nH	Measured from Drain lead (6mm /0.25in from pack.) to Source lead (6mm/0.25in from pack.) with Source wire internally bonded from Source pin to Drain pad
C <sub>iss</sub>	Input Capacitance	—	611	—	pF	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 25V f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	62	—		
C <sub>rss</sub>	Reverse Transfer Capacitance	—	0.64	—		
R <sub>g</sub>	Gate Resistance	—	8.0	—	Ω	f = 1.0MHz, open drain

## Source-Drain Diode Ratings and Characteristics

	Parameter	Min	Typ	Max	Units	Test Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	3.3	A	T <sub>j</sub> = 25°C, I <sub>S</sub> = 3.3A, V <sub>GS</sub> = 0V ④
I <sub>SM</sub>	Pulse Source Current (Body Diode) ①	—	—	13.2		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.2	V	T <sub>j</sub> = 25°C, I <sub>F</sub> = 3.3A, di/dt ≤ 100A/μs
t <sub>rr</sub>	Reverse Recovery Time	—	—	371	ns	V <sub>DD</sub> ≤ 25V ④
Q <sub>RR</sub>	Reverse Recovery Charge	—	—	1.05	μC	
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L <sub>S</sub> + L <sub>D</sub> .				

## Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R <sub>thJC</sub>	Junction-to-Case	—	—	5.5	°C/W	

Note: Corresponding Spice and Saber models are available on International Rectifier Web site.

For footnotes refer to the last page

## Radiation Characteristics

IRHLF77214, 2N7610T2

International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-39 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

**Table 1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation ⑤⑥**

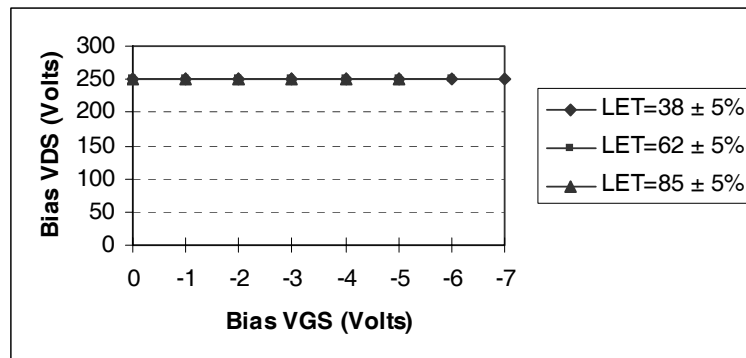
	Parameter	Up to 300K Rads(Si) <sup>1</sup>		Units	Test Conditions
		Min	Max		
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	250	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
V <sub>GS(th)</sub>	Gate Threshold Voltage	1.0	2.0		V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250μA
I <sub>GSS</sub>	Gate-to-Source Leakage Forward	—	100	nA	V <sub>GS</sub> = 10V
I <sub>GSS</sub>	Gate-to-Source Leakage Reverse	—	-100		V <sub>GS</sub> = -10V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	—	1.0	μA	V <sub>DS</sub> = 200V, V <sub>GS</sub> = 0V
R <sub>DS(on)</sub>	Static Drain-to-Source On-State Resistance (TO-39) ④	—	1.0	Ω	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 2.1A
V <sub>SD</sub>	Diode Forward Voltage ④	—	1.2	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 3.3A

1. Part numbers IRHLF77214, IRHLF73214

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

**Table 2. Typical Single Event Effect Safe Operating Area**

LET (MeV/(mg/cm <sup>2</sup> ))	Energy (MeV)	Range (μm)	VDS (V)					
			@VGS=0V	@VGS=-2V	@VGS=-4V	@VGS=-5V	@VGS=-6V	@VGS=-7V
38 ± 5%	300 ± 7.5%	38 ± 7.5%	250	250	250	250	250	250
62 ± 5%	355 ± 7.5%	33 ± 7.5%	250	250	250	250	250	-
85 ± 5%	380 ± 7.5%	29 ± 7.5%	250	250	250	250	-	-



**Fig a. Typical Single Event Effect, Safe Operating Area**

For footnotes refer to the last page

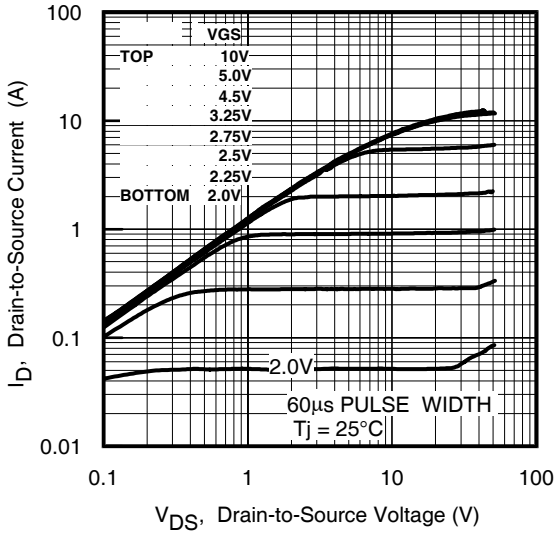


Fig 1. Typical Output Characteristics

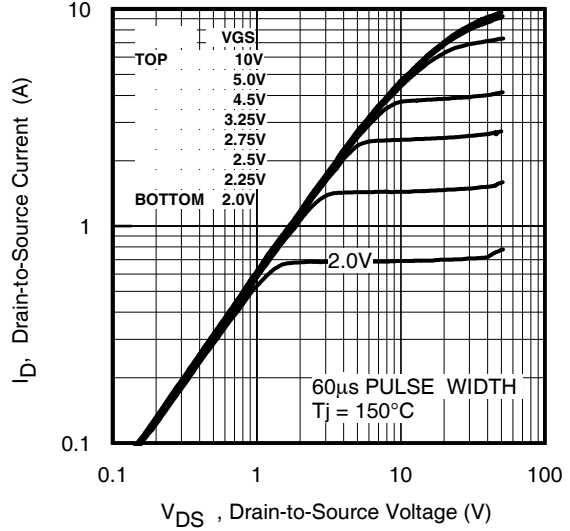


Fig 2. Typical Output Characteristics

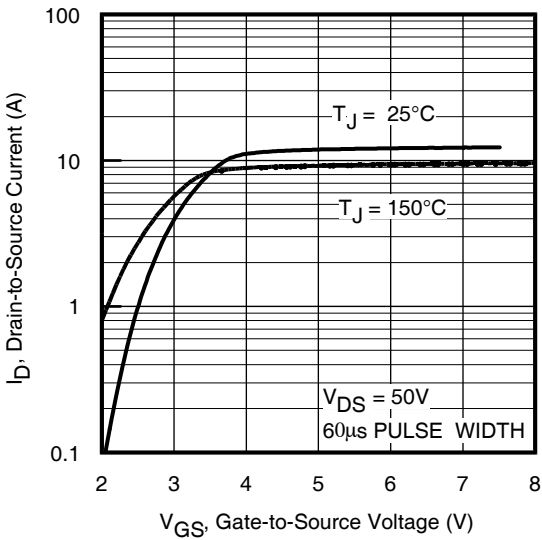


Fig 3. Typical Transfer Characteristics

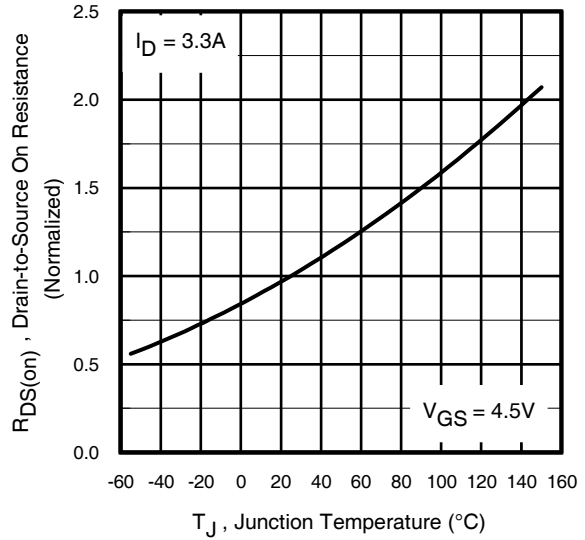


Fig 4. Normalized On-Resistance Vs. Temperature

Pre-Irradiation

IRH77214, 2N7610T2

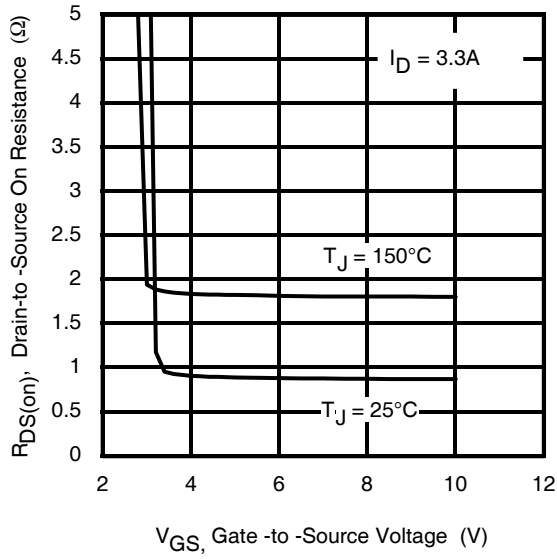


Fig 5. Typical On-Resistance Vs Gate Voltage

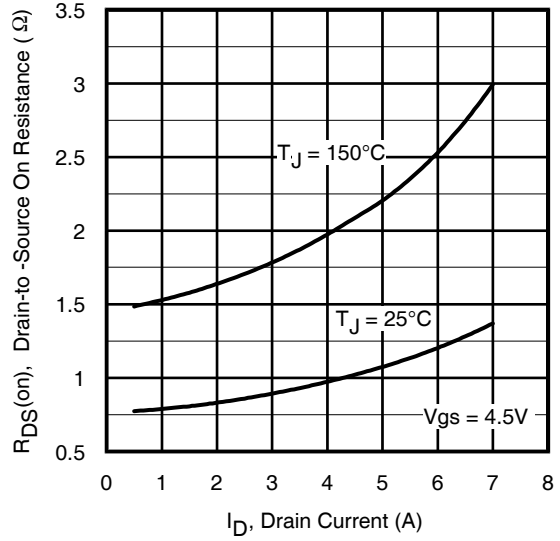


Fig 6. Typical On-Resistance Vs Drain Current

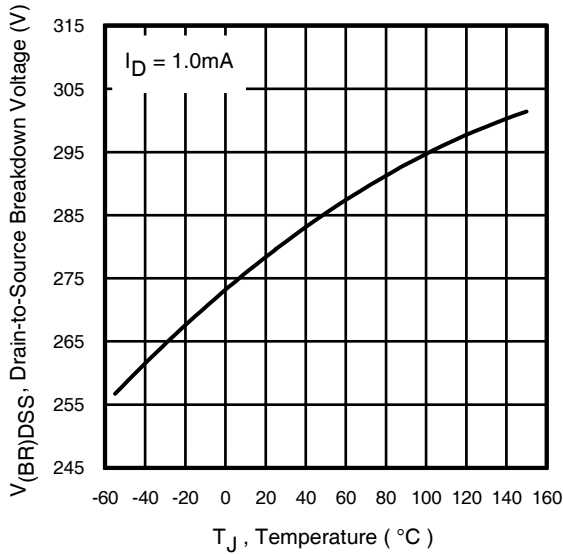


Fig 7 Typical Drain-to-Source Breakdown Voltage Vs Temperature

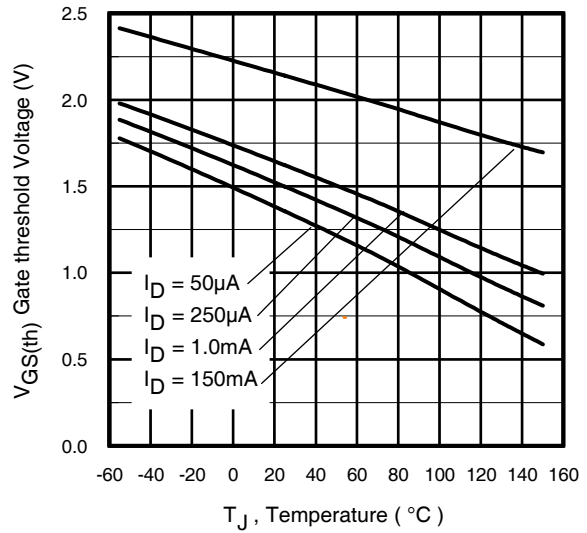
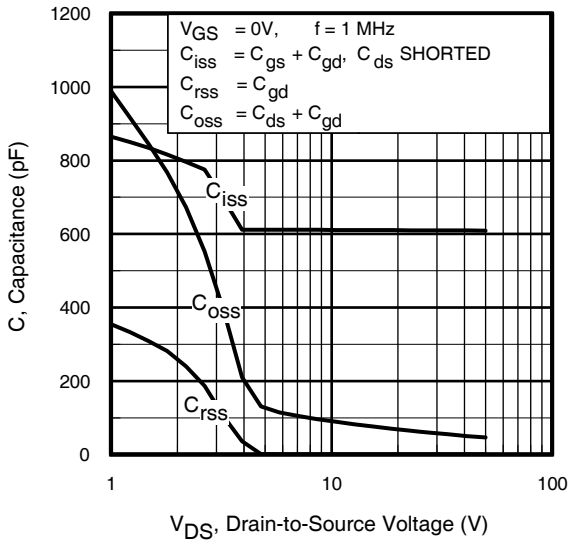
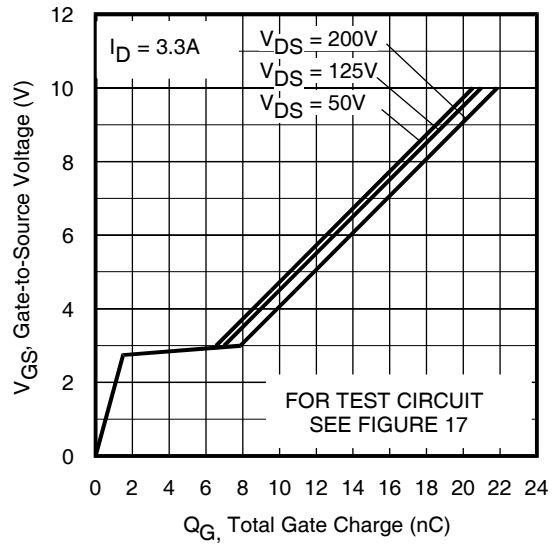


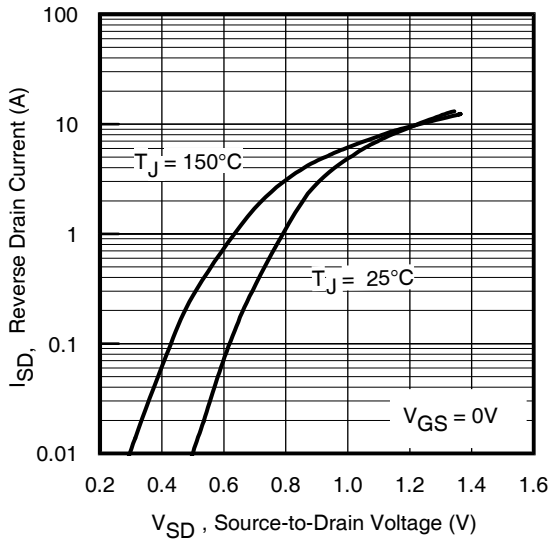
Fig 8. Typical Threshold Voltage Vs Temperature



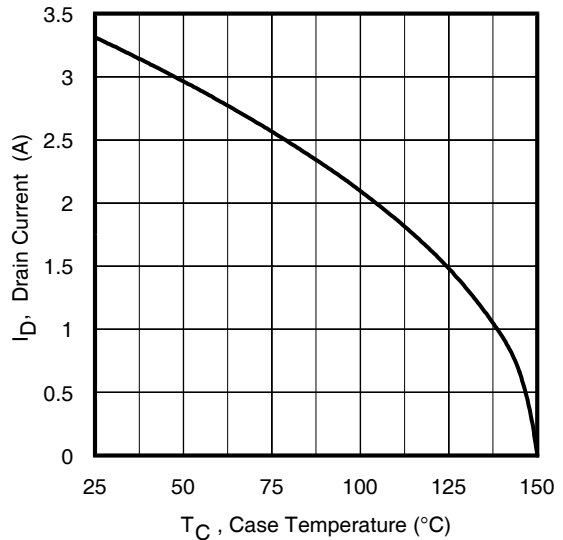
**Fig 9.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 10.** Typical Gate Charge Vs. Gate-to-Source Voltage



**Fig 11.** Typical Source-to-Drain Diode Forward Voltage



**Fig 12.** Maximum Drain Current Vs. Case Temperature

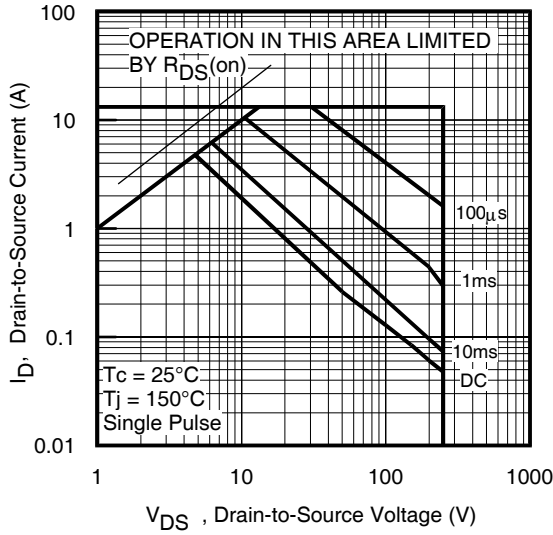


Fig 13. Maximum Safe Operating Area

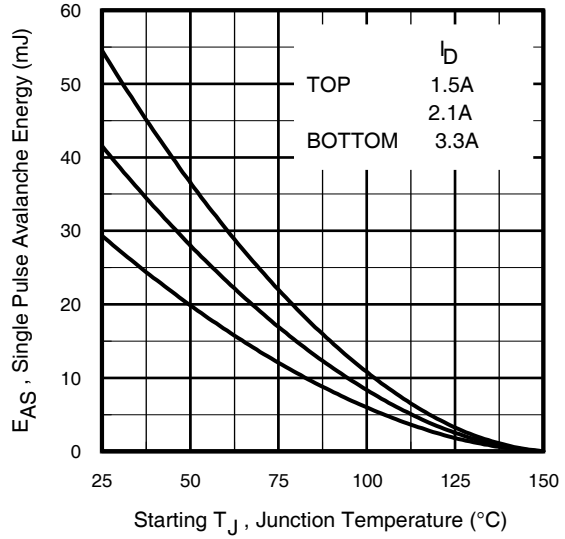


Fig 14. Maximum Avalanche Energy Vs. Drain Current

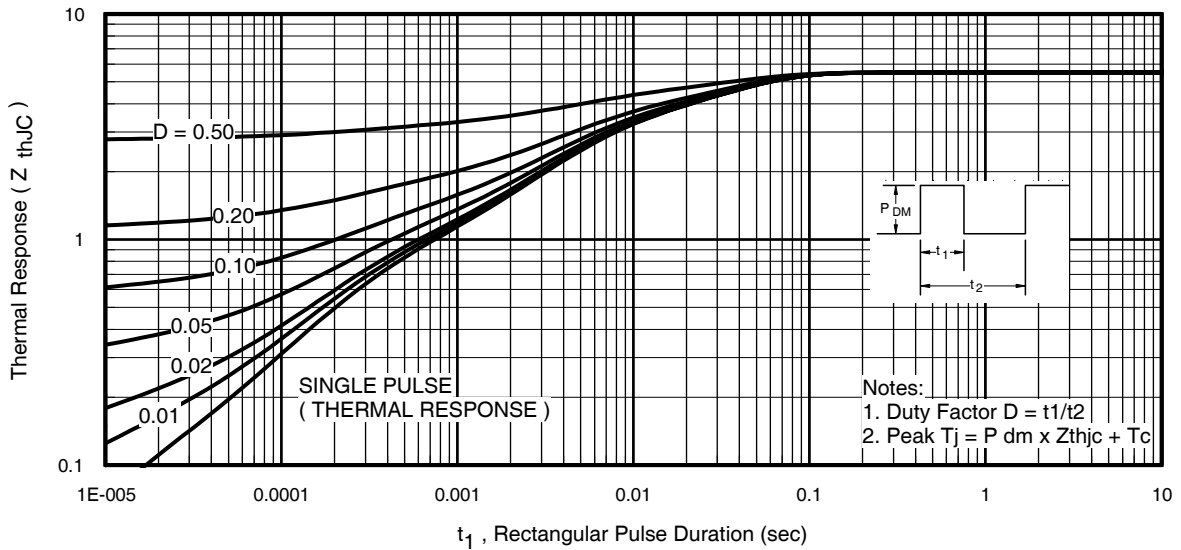


Fig 15. Maximum Effective Transient Thermal Impedance, Junction-to-Case

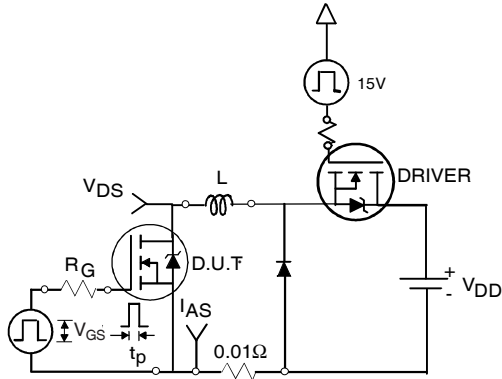


Fig 16a. Unclamped Inductive Test Circuit

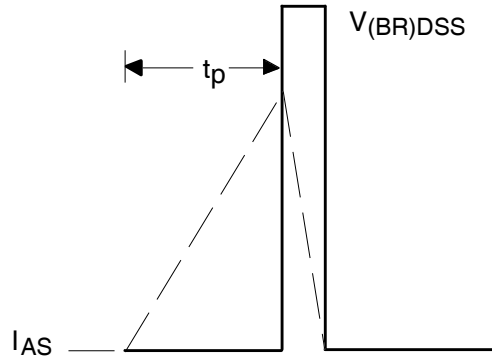


Fig 16b. Unclamped Inductive Waveforms

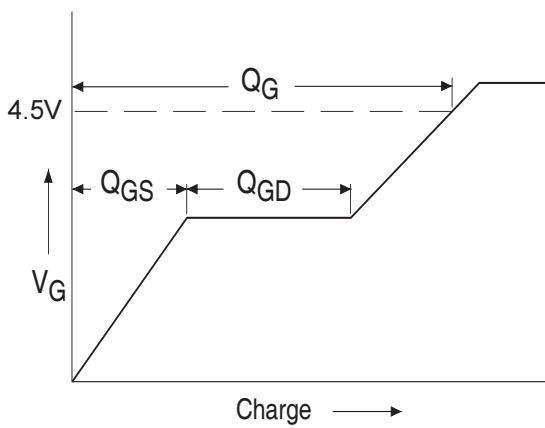


Fig 17a. Basic Gate Charge Waveform

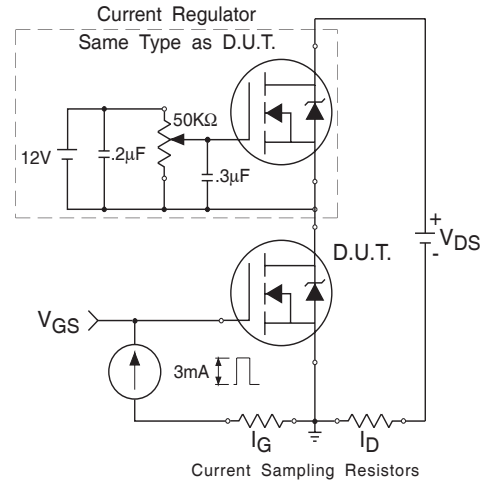


Fig 17b. Gate Charge Test Circuit

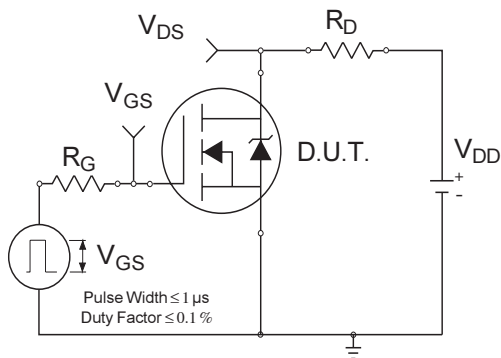


Fig 18a. Switching Time Test Circuit

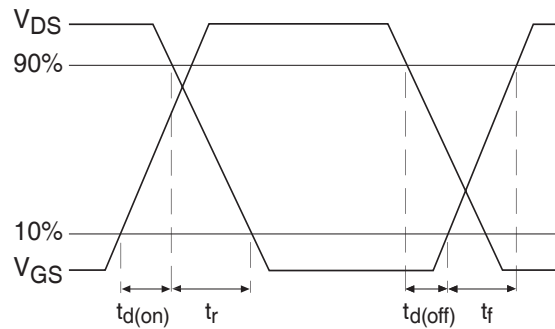


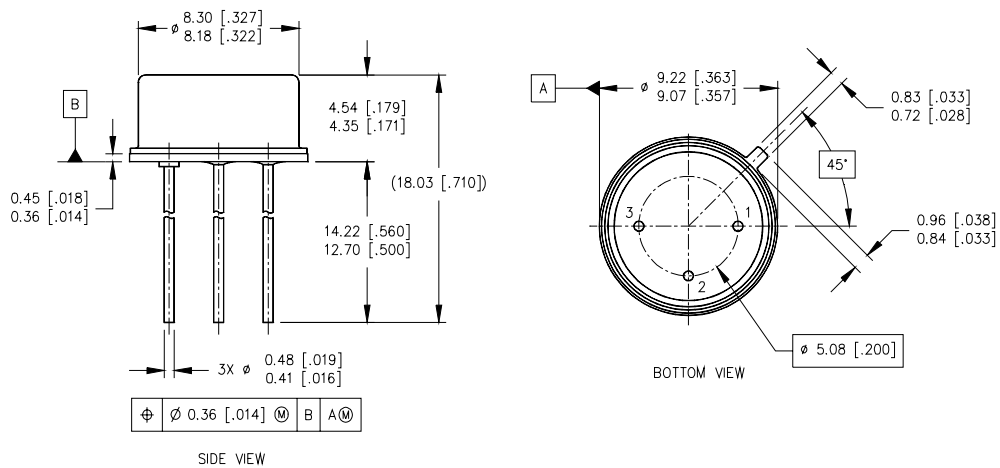
Fig 18b. Switching Time Waveforms



**Footnotes:**

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ②  $V_{DD} = 50V$ , starting  $T_J = 25^\circ C$ ,  $L = 5.4mH$   
Peak  $I_L = 3.3A$ ,  $V_{GS} = 10V$
- ③  $ISD \leq 3.3A$ ,  $di/dt \leq 372A/\mu s$ ,  
 $V_{DD} \leq 250V$ ,  $T_J \leq 150^\circ C$
- ④ Pulse width  $\leq 300 \mu s$ ; Duty Cycle  $\leq 2\%$
- ⑤ **Total Dose Irradiation with  $V_{GS}$  Bias.**  
10 volt  $V_{GS}$  applied and  $V_{DS} = 0$  during irradiation per MIL-STD-750, method 1019, condition A.
- ⑥ **Total Dose Irradiation with  $V_{DS}$  Bias.**  
200 volt  $V_{DS}$  applied and  $V_{GS} = 0$  during irradiation per MIL-STD-750, method 1019, condition A.

**Case Outline and Dimensions — TO-205AF (Modified TO-39)**



International  
**IOR** Rectifier

**IR WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
**IR LEOMINSTER :** 205 Crawford St., Leominster, Massachusetts 01453, USA Tel: (978) 534-5776  
TAC Fax: (310) 252-7903

Visit us at [www.irf.com](http://www.irf.com) for sales contact information.  
Data and specifications subject to change without notice. 02/2012

单击下面可查看定价，库存，交付和生命周期等信息

[>>Infineon Technologies\(英飞凌\)](#)